

### **INCHANGE SEMICONDUCTOR**

# isc N-Channel MOSFET Transistor

### IXTP200N085T

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Ros( • Fully ch • 100% a • Minimu perform • <b>APPLI</b>	train-source on-resistance: on) ≤ 5.0mΩ@V <sub>GS</sub> =10V naracterized avalanche voltage and c avalanche tested im Lot-to-Lot variations for robust dev nance and reliable operation			pin 1, Gate 1 2 3 1 2 2 1 2 2 1 2 3 2, Drain 3, Source TO-220C package
<ul> <li>DC/DC</li> </ul>	Converters			
-	urrent Switching Applications _UTE MAXIMUM RATINGS(Ta=25°C			
SYMBOL	PARAMETER	VALUE	UNIT	ψ .
V <sub>DSS</sub>	Drain-Source Voltage	85	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	y   15,02,0 y   15,02,0 y   15,02,0
I <sub>D</sub>	Drain Current-Continuous	200	А	
I <sub>DM</sub>	Drain Current-Single Pulsed	540	A	↑ mm
PD	Total Dissipation @Tc=25℃	480	W	DIM MIN MAX A 15.50 15.90 B 9.90 10.20
Tj	Operating Junction Temperature	-55~175	°C	C 4.20 4.50 D 0.70 0.90
T <sub>stg</sub>	Storage Temperature	-55~175	°C	F         3.40         3.70           G         4.98         5.18           H         2.68         2.90
• THERM	IAL CHARACTERISTICS			J 0.44 0.60 K 13.00 13.40 L 1.10 1.45

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SYMBOL	MBOL PARAMETER		UNIT	
R <sub>th(j-c)</sub>	R <sub>th(j-c)</sub> Junction-to-case thermal resistance		°C/W	

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Q

R

U

v

2.70

2.30

1.29

6.45 8.66 2.90

2.70

1.35

6.65

8.86



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#### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V; ID = 250 μ A	85		V
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; ID = 250 μ A	2.0	4.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> = 25A		5.0	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V		±200	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V	5		
		V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V;T <sub>J</sub> = 150°C		250	μA
Vsd	Diode forward voltage	I <sub>F</sub> = 25A; V <sub>GS</sub> = 0V		1.0	V

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